

What is claimed is:

1. A semiconductor light emitting device comprising:

a semiconductor substrate;

a semiconductor laminating portion formed on said
5 semiconductor substrate, said semiconductor laminating
portion including a light emitting layer forming portion
having at least an n-type layer and a p-type layer;

a current diffusing electrode formed on said
semiconductor laminating portion, said current diffusing
10 electrode exhibiting translucency and electric conductivity;

a bonding electrode formed on a part of said current
diffusing electrode; and

an electrode formed on a rear surface of said
semiconductor substrate,

15 wherein said semiconductor laminating portion and
said current diffusing electrode are separated into a
plurality of light emitting unit portions, an electrode pad
portion, and connecting portions for connecting between said
electrode pad portion and said light emitting unit portions
20 or between two of said light emitting unit portions, and

wherein said bonding electrode is provided on said
electrode pad portion, and said electrode pad portion is formed
so as to make said light emitting layer forming portion in
said electrode pad portion be nonluminous.

25 2. The semiconductor light emitting device of claim
1, wherein said connecting portions are formed so as to make

said light emitting layer forming portion in each of said connecting portions be nonluminous.

3. The semiconductor light emitting device of claim 2, wherein a metallic electrode is formed on said current
5 diffusing electrode of each of said connecting portions.

4. The semiconductor light emitting device of claim 1, wherein a current blocking layer is formed on one layer between said current diffusing electrode and said semiconductor substrate to be nonluminous.

10 5. The semiconductor light emitting device of claim 4, wherein said current blocking layer is an electrically-insulating layer, or a semiconductor layer that has different conductivity from that of semiconductor layers adjoining to said current blocking layer.

15 6. The semiconductor light emitting device of claim 1, wherein when the planar shape of each of said light emitting unit portions is circular, the size of each of said light emitting unit portions is defined such that the diameter thereof is not more than six times of the thickness of said
20 semiconductor laminating portion.

7. The semiconductor light emitting device of claim 6, wherein the thickness of said semiconductor laminating portion is approximately 3 to 10 μm and the diameter of each of said light emitting unit portions is approximately 10 to
25 50 μm .

8. The semiconductor light emitting device of claim 1, wherein when the planar shape of each of said light emitting

unit portions is rectangular or elliptic, the size of each of said light emitting unit portions is defined such that a longer side or a longer diameter thereof is not more than six times of the thickness of said semiconductor laminating portion.

9. The semiconductor light emitting device of claim 1, wherein a distance between adjoining two of said light emitting unit portions is defined to be not less than twice of the thickness of said semiconductor laminating portion.

10. The semiconductor light emitting device of claim 1, wherein said current diffusing electrode is made of an Au-Ge or Au-Ni alloy layer having a thickness of 2 to 100 nm.

11. The semiconductor light emitting device of claim 1, wherein said current diffusing electrode is an ITO film.

12. The semiconductor light emitting device of claim 1, wherein said semiconductor laminating portion is made of an InGaAlP based material or an AlGaAs based material.